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Query/Command : file pluspat

Selected file: PLUSPAT

Search statement   1

Query/Command : us5283761/pn

* SS 3: Results 1

Search statement   4

Query/Command : prt fu legalall max

1 / 1   PLUSPAT - ©QUESTEL-ORBIT - image
PN   -   US5283761 A 19940201 [US5283761]
TI   -   (A) Method of multi-level storage in DRAM
PA   -   (A) MOSAID TECHNOLOGIES INC   (CA)
PA0 -   Mosaid Technologies Incorporated, Ontario [CA]
IN   -   (A) GILLINGHAM PETER B   (CA)
AP   -   US91667392   19920722   [1992US-0916673]
PR   -   US91667392   19920722   [1992US-0916673]
IC   -   (A) G11C-007/00
EC   -   G11C-011/56E
PCL -   ORIGINAL (O) : 365189070; CROSS-REFERENCE (X) : 327051000
         365149000 365168000 365189090 365233500
DT   -   Basic
CT   -   US4287570; US4415992; US4661929; US4771404; US5184324
STG -   (A) United States patent
AB   -   A method of processing data having one of four voltage levels
         stored in a DRAM cell is comprised of sensing whether or not the
         data voltage is above or below a voltage level midway between a
         highest and a lowest of the four levels, setting the voltage on a
         reference line higher than the lowest and lower than the next
         highest of the four levels in the event the data voltage is below
         the midway voltage level, and setting the voltage on the reference
         line higher than the second highest and lower than the highest of
         the four levels in the event the data voltage is above the midway
         point, and sensing whether the data voltage is higher or lower
         than the reference line, whereby which of the four levels the data
         occupies is read.

1 / 1   LGST - ©EPO
PN   -   US5283761 A 19940201 [US5283761]
AP   -   US91667392   19920722   [1992US-0916673]
ACT -   19920722 US/AS02-A
         ASSIGNMENT OF ASSIGNOR'S INTEREST
         OWNER: MOSAID TECHNOLOGIES INCORPORATED P.O. BOX 13579 KA;
         EFFECTIVE DATE: 19920707

         19920722 US/AS02-A
         ASSIGNMENT OF ASSIGNOR'S INTEREST
         OWNER: GILLINGHAM, PETER B.; EFFECTIVE DATE: 19920707

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               19960514  US/RF-A
               REISSUE APPLICATION FILED
               EFFECTIVE DATE: 19960131
UP  -    2003-22




1 / 1    CRXX - ©CLAIMS/RRX
AN  -    2441799
PN  -    5,283,761 A  19940201  [US5283761]
PA  -    Mosaid Technologies Inc CA
PT  -    E (Electrical)
ACT -    19960131  REISSUE REQUESTED
         ISSUE DATE OF O.G.: 19960514
         REISSUE REQUEST NUMBER: 08/595020
         EXAMINATION GROUP RESPONSIBLE FOR REISSUEPROCESS: 2511
         Reissue Patent Number: USRE37072


UP  -    1999-00
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Search statement   4

Query/Command : fam us5283761/pn

1 Patent Groups
** SS 4: Results 2

Search statement   5

Query/Command : famstate nonstop

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1 / 2    PLUSPAT - ©QUESTEL-ORBIT - image
PN  -    USRE37072 E1 20010227 [USRE37072]
STG -    (E1) Reissue Patent
TI  -    (E1) Method of multi-level storage in DRAM and apparatus thereof
PA  -    (E1) MOSAID TECHNOLOGIES INC   (US)
PA0 -    Mosaid Technologies, Inc., Kanata [CA]
IN  -    (E1) GILLINGHAM PETER B   (CA)
IC  -    (E1) G11C-007/00
AP  -    US59502096  19960131   [1996US-0595020]
PR  -    US59502096  19960131   [1996US-0595020]
         US91667392  19920722   [1992US-0916673]
EC  -    G11C-011/56E
PCL -    ORIGINAL (O) : 365189070; CROSS-REFERENCE (X) : 327052000
         327056000  365149000  365168000  365189090  365190000
DT  -    Corresponding document
UP  -    2001-14



2 / 2    PLUSPAT - ©QUESTEL-ORBIT - image
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PN  -   US5283761 A 19940201 [US5283761]
STG -   (A) United States patent
TI  -   (A) Method of multi-level storage in DRAM
PA  -   (A) MOSAID TECHNOLOGIES INC  (CA)
PAO -   Mosaid Technologies Incorporated, Ontario [CA]
IN  -   (A) GILLINGHAM PETER B  (CA)
IC  -   (A) G11C-007/00
AP  -   US91667392  19920722  [1992US-0916673]
PR  -   US91667392  19920722  [1992US-0916673]
EC  -   G11C-011/56E
PCL -   ORIGINAL (O) : 365189070; CROSS-REFERENCE (X) : 327051000
        365149000  365168000  365189090  365233500
DT  -   Basic
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1 / 1   LEGALI - ©EPO
PN  -   US5283761 A 19940201 [US5283761]
AP  -   US91667392  19920722  [1992US-0916673]
ACTE-   19920722  US/AS02-A
        ASSIGNMENT OF ASSIGNOR'S INTEREST
        OWNER: MOSAID TECHNOLOGIES INCORPORATED P.O. BOX 13579 KA;
        EFFECTIVE DATE: 19920707

        19920722  US/AS02-A
        ASSIGNMENT OF ASSIGNOR'S INTEREST
        OWNER: GILLINGHAM, PETER B.; EFFECTIVE DATE: 19920707

        19960514  US/RF-A
        REISSUE APPLICATION FILED
        EFFECTIVE DATE: 19960131
UP  -   2003-22
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WELCOME to QUESTEL.ORBIT- Your Guide to INTELLECTUAL PROPERTY

Query/Command : file pluspat

Selected file: PLUSPAT

Search statement   1   ·

Query/Command : re37072/pn

** SS 1: Results 1

Search statement   2

Query/Command : prt fu legalall max

1 / 1   PLUSPAT - ©QUESTEL-ORBIT - image
PN   -   USRE37072 E1 20010227 [USRE37072]
TI   -   (E1) Method of multi-level storage in DRAM and apparatus thereof
PA   -   (E1) MOSAID TECHNOLOGIES INC (US)
PAO -   Mosaid Technologies, Inc., Kanata [CA]
IN   -   (E1) GILLINGHAM PETER B (CA)
AP   -   US59502096 19960131 [1996US-0595020]
FD   -   Reissued: US916673 19920722 [1992US-0916673]
         Reissue of: US5283761 - 19940201
PR   -   US59502096 19960131 [1996US-0595020]
         US91667392 19920722 [1992US-0916673]
IC   -   (E1) G11C-007/00
EC   -   G11C-011/56E
PCL -   ORIGINAL (O) : 365189070; CROSS-REFERENCE (X) : 327052000
         327056000 365149000 365168000 365189090 365190000
DT   -   Corresponding document
CT   -   US4287570; US4415992; US4622655; US4661929; US4771404; US5184324;
US5293563
         Ohta, Yoshiji et al., Symposium, "A Novel Memory Cell Architecture
         for High-Density DRAMs," VLSI Circuits, May 1989, pp. 101-102.
STG -   (E1) Reissue Patent
AB   -   A method of processing data having one of four voltage levels
         stored in a DRAM cell is comprised of sensing whether or not the
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         than the reference line, whereby which of the four levels the data
         occupies is ·read.
UP   -   2001-14

1 / 1   CRXX - ©CLAIMS/RRX
AN   -   3466983
PN   -   37,072   E 20010227 [USRE37072]
PA   -   Mosaid Technologies Inc CA
PT   -   . E (Electrical)

ACT – 20011218 CERTIFICATE OF CORRECTION

UP – 2001-51
UCOR– 2001-12-18

Search statement 2

Query/Command : fam re37072/pn

 1 Patent Groups
 ** SS 2: **Results 2**

Search statement 3

Query/Command : famstate nonstop

1 / 2 PLUSPAT – ©QUESTEL-ORBIT – image
PN – USRE37072 E1 20010227 [USRE37072]
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     US91667392 19920722 [1992US-0916673]
EC – G11C-011/56E
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     327056000 365149000 365168000 365189090 365190000
DT – Corresponding document
UP – 2001-14

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PR – US91667392 19920722 [1992US-0916673]
EC – G11C-011/56E
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     365149000 365168000 365189090 365233500
DT – Basic

1 / 1 LEGALI – ©EPO

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          ASSIGNMENT OF ASSIGNOR'S INTEREST
          OWNER: GILLINGHAM, PETER B.; EFFECTIVE DATE: 19920707

          19960514 US/RF-A
          REISSUE APPLICATION FILED
          EFFECTIVE DATE: 19960131
UP –   2003-22

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